

**NITRIDE SEMICONDUCTOR DEVICE**

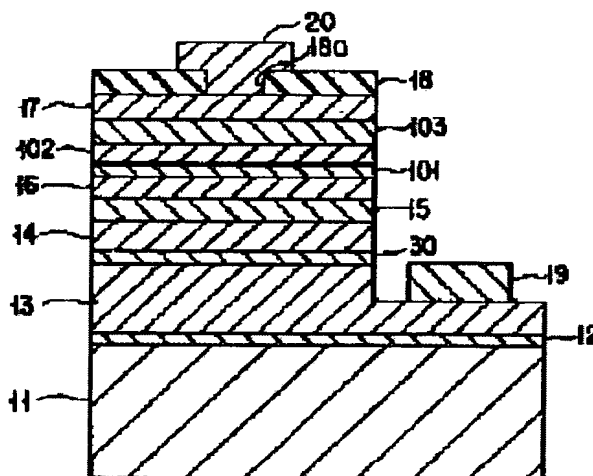
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**Abstract of JP10126006**

**PROBLEM TO BE SOLVED:** To provide a high luminous-efficiency nitride semiconductor device which has an active layer containing nitride semiconductor including indium.

**SOLUTION:** A first nitride semiconductor layer 101 having band gap energy higher than that of an active layer 16 is formed on at least one surface of the active layer 16. Further a second nitride semiconductor layer 102 having band gap energy lower than that of the first nitride semiconductor layer 101, and a third nitride semiconductor layer 103 having band gap energy higher than that of the second nitride semiconductor layer 102, are formed on the first nitride semiconductor layer 101.



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